

UNISONIC TECHNOLOGIES CO., LTD

UT4101 Power MOSFET

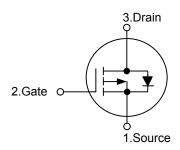
P-CHANNEL ENHANCEMENT MODE

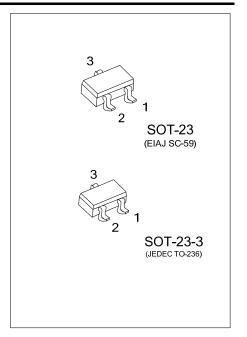
■ DESCRIPTION

The UTC **UT4101** is P-channel enhancement mode Power MOSFET, designed with high density cell, with fast switching speed, low on-resistance, excellent thermal and electrical capabilities and operation with low gate voltages.

This device is suitable for use as a load switch or in PWM applications.

■ SYMBOL

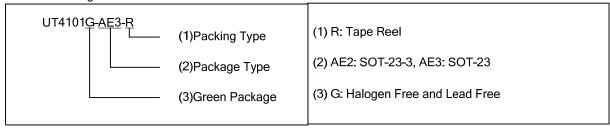




ORDERING INFORMATION

Ordering Number	Package	Pin Assignment			Daakina	
		1	2	3	Packing	
UT4101G-AE2-R	SOT-23-3	S	G	D	Tape Reel	
UT4101G-AE3-R	SOT-23	S	G	D	Tape Reel	

Note: Pin Assignment: G: Gate D: Drain S: Source



■ MARKING



UT4101 Power MOSFET

■ ABSOLUTE MAXIMUM RATINGS (T_J = 25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATING	UNITS
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V _{GS}	±8.0	V
Continuous Drain Current (Note 3)	I _D	-2.4	Α
Pulsed Drain Current (Note 1, 2)	I _{DM}	-7.5	Α
Power Dissipation	P_{D}	1.25	W
Junction Temperature	T_J	+150	Ŝ
Storage Temperature	T _{STG}	-55 ~ + 150	Ô

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT
Junction-to-Ambient	θ_{JA}	100	°C/W

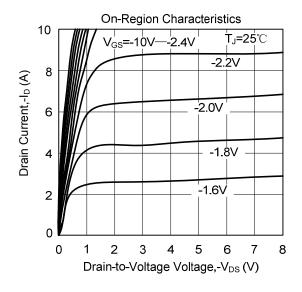
■ **ELECTRICAL CHARACTERISTICS** (T_A =25°C, unless otherwise specified)

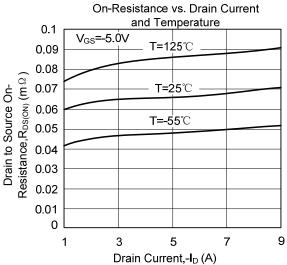
OFF CHARACTERISTICS Drain-Source Breakdown Voltage BV _{DSS} V _{GS} = 0 V, I _D = -250µA -20 -1.0 Drain-Source Leakage Current I _{DSS} V _{DS} = -16 V, V _{GS} = 0 V -1.0 -1.0 Gate-Source Leakage Current I _{DSS} V _{DS} = -16 V, V _{GS} = ±8.0 V ±100 ON CHARACTERISTICS Gate Threshold Voltage V _{GS(TH)} V _{DS} = V _{GS} , I _D = -250 µA -0.40 -0.72 -1.5 Vase = -4.5 V, I _D = -1.6 A 70 85 1 Drain-Source On-State Resistance (Note 2) R _{DS(ON)} V _{DS} = -2.5 V, I _D = -1.6 A 70 85 1 DYNAMIC PARAMETERS Input Capacitance C _{ISS} V _{DS} = -1.8 V, I _D = -0.9 A 112 210 1 DYNAMIC PARAMETERS Input Capacitance C _{ISS} V _{DS} = -10 V, V _{GS} = 0V, I _D = -10 V, V _{GS} = 0V, I = -10 V, I _D =							
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	OFF CHARACTERISTICS						
	Drain-Source Breakdown Voltage	BV_{DSS}	V _{GS} =0 V, I _D =-250μA	-20			V
ON CHARACTERISTICS Cate Threshold Voltage $V_{GS(TH)}$ $V_{DS} = V_{GS}$, $I_D = -250 \mu A$ -0.40 -0.72 -1.5 Drain-Source On-State Resistance (Note 2) $R_{DS(ON)}$ $V_{GS} = -4.5 \text{ V}$, $I_D = -1.6 \text{ A}$ 70 85 10 DYNAMIC PARAMETERS $V_{GS} = -2.5 \text{ V}$, $I_D = -0.9 \text{ A}$ 112 210 10 Input Capacitance C_{ISS} $V_{DS} = -10 \text{ V}$, $V_{GS} = 0V$, $V_{CS} = $	Drain-Source Leakage Current	I _{DSS}	V _{DS} =-16 V, V _{GS} =0 V			-1.0	μΑ
Gate Threshold Voltage $V_{GS(TH)}$ $V_{DS} = V_{GS}$, $I_D = -250 \mu A$ -0.40 -0.72 -1.5 Drain-Source On-State Resistance (Note 2) $R_{DS(ON)}$ $V_{GS} = -4.5 V$, $I_D = -1.6 A$ 70 85 1 DYNAMIC PARAMETERS $V_{GS} = -2.5 V$, $I_D = -1.3 A$ 90 120 1 Input Capacitance C_{ISS} $V_{DS} = -1.8 V$, $I_D = -0.9 A$ 112 210 1 Output Capacitance C_{ISS} $V_{DS} = -1.0 V$, $V_{GS} = 0V$, $V_{DS} = -10 V$, $V_{GS} = 0V$, $V_{DS} = -10 V$, V_{DS	Gate-Source Leakage Current	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8.0 \text{ V}$			±100	nA
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	ON CHARACTERISTICS						
$ \begin{array}{ c c c c c c c c } \hline Drain-Source On-State Resistance (Note 2) & R_{DS(ON)} & V_{GS} = -2.5 \text{ V}, I_D = -1.3 \text{ A} & 90 & 120 & 100 $	Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-0.40	-0.72	-1.5	V
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$			V_{GS} =-4.5 V, I_{D} =-1.6 A		70	85	mΩ
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Drain-Source On-State Resistance (Note 2)	$R_{DS(ON)}$	V_{GS} =-2.5 V, I_{D} =-1.3 A		90	120	mΩ
	. ,		V_{GS} =-1.8 V, I_{D} =-0.9 A		112	210	mΩ
Output Capacitance C_{OSS} $f=10 \text{ V}, V_{GS}=0 \text{ V}, f=100 100 \text$	DYNAMIC PARAMETERS						
	Input Capacitance	C_{ISS}	- 40 -0 \		675		pF
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Output Capacitance	Coss	1 , ,		100		pF
	Reverse Transfer Capacitance		I – IIVITIZ		75		pF
	SWITCHING PARAMETERS						
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Turn-ON Delay Time	$t_{D(ON)}$	15/1/ 10/15		7.5		ns
Turn-OFF Delay Time $t_{D(OFF)}$ I_{D} =-1.6A30.2Turn-OFF Fall-Time t_{F} 21.0	Turn-ON Rise Time	t_R			12.6		ns
Turn-OFF Fall-Time t_F V_{DS} =-10 V, V_{GS} =-4.5 V, I_D 7.5 8.5	Turn-OFF Delay Time	t _{D(OFF)}	,		30.2		ns
	Turn-OFF Fall-Time	t_{F}	ID1.0A		21.0		ns
	Gate Charge	Q_G			7.5	8.5	nC
Gate Source Charge Q _{GS} V = 10 V I = 1.64 1.2	Gate Source Charge	Q_GS	V - 40 V I - 4 CA		1.2		nC
$V_{D} = V_{D} = V_{D$	Gate Drain Charge		V _{DS} =-10 V, I _D =-1.6A		2.2		nC
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS	SOURCE- DRAIN DIODE RATINGS AND CH	HARACTERI	STICS				
Drain-Source Diode Forward Voltage(Note2) V _{SD} V _{GS} =0V, I _S =-2.4 A -0.82 -1.2	Drain-Source Diode Forward Voltage(Note2)	V_{SD}	V _{GS} =0V, I _S =-2.4 A		-0.82	-1.2	V
Maximum Continuous Drain-Source Diode Forward Current		I _S				-2.4	Α
Reverse Recovery Time $t_{RR} = V_{GS} = 0V, \ dI_{SD}/dt = 100A/\mu s, \\ I_{S} = -1.6A \qquad 12.8 15$	Reverse Recovery Time	t _{RR}	· · ·		12.8	15	ns
Reverse Recovery Charge Q _{RR} 1008	Reverse Recovery Charge	Q _{RR}			1008		nC

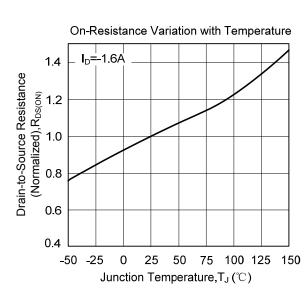
Notes: 1. Pulse width limited by $T_{J(MAX)}$

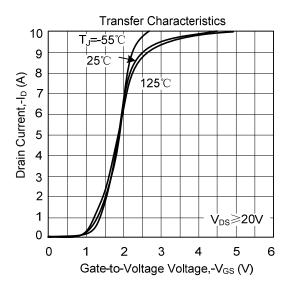
- 2. Pulse width ≤300us, duty cycle ≤2%.
- 3. Surface mounted on 1 in² copper pad of FR4 board.

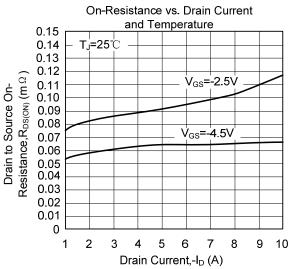
■ TYPICAL CHARACTERISTICS

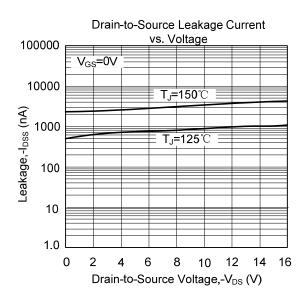






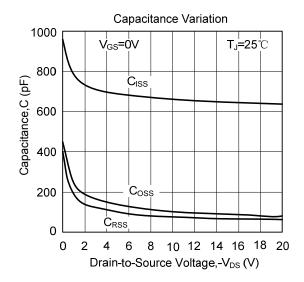


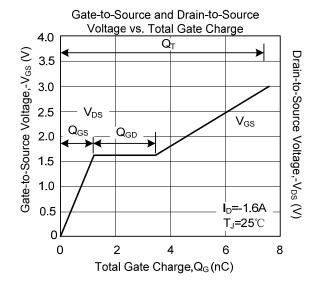


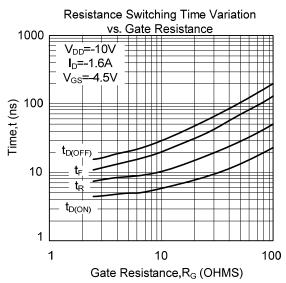


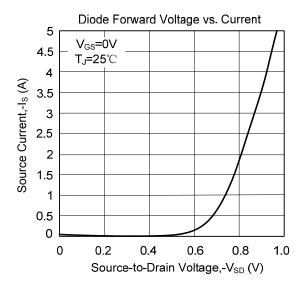
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■ TYPICAL CHARACTERISTICS(Cont.)









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